

-In recent years, various fine processing techniques have been researched and developed for advanced high integration and high performance of LSI wherein LSI stands for "Large Scale Integration".

A Among them, the chemical mechanical polishing (hereafter, may be abbreviated as CMP) has been attracting the attention. CMP is a composite technique involving a chemical action and a mechanical action between a polishing composition and a material to be polished. It is an essential technique in the planarizing of insulating interlayers, particularly in the multilayer wiring formation step, in the metal plug formation, in the buried-type metal wiring formation and the like.--

Please replace the paragraph starting at page 8, line 20 and spanning to page 9, line 2 with the following rewritten paragraph.

A2 -The functional group capable of trapping a metal ion preferably exists on the surface of the particle. Even if the group does not exist on the surface of the particle, the same effect can be obtained when the functional group capable of trapping a metal ion can appear on the surface of the particle and can contact with a metal to be polished by crushing of the particle due to stress on polishing, by peeling of a coating film or by other situations.--